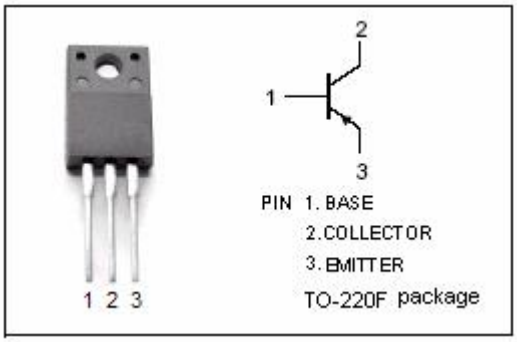
isc Silicon PNP Power Transistor 2SA1659

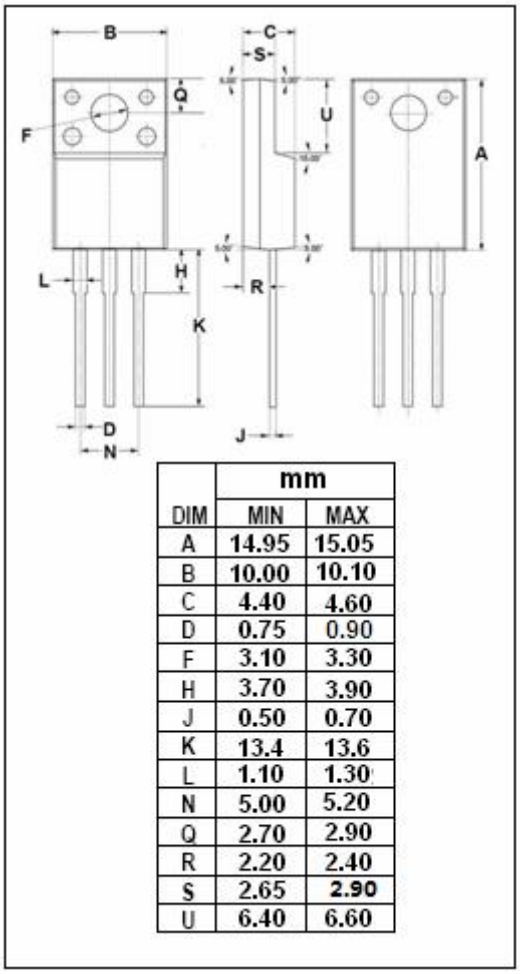


DESCRIPTION

- High Collector-Emitter Breakdown Voltage
  V_{CEO}= -160V(Min)
- Complement to Type 2SC4370
- Full-mold package that does not require an insulating board or bushing when mounting.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high voltage applications



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
$I_{C(DC)}$	Collector Current(DC)	-1.5	A
$I_{B(DC)}$	Base Current	-0.15	A
P_C	Collector Power Dissipation @T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-160			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -160V ; I_E=0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-1.0	μA
h_{FE}	DC Current Gain	I_C= -100mA ; V_{CE}= -5V	70		240	
C_{OB}	Output Capacitance	I_E=0 ; V_{CB}= -10V;f= 1.0MHz		30		pF
f_T	Current-Gain—Bandwidth Product	I_C=-100m A ; V_{CE}= -10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240